

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

DESCRIPTION

This product is Dual N-channel MOS Field Effect Transistor designed for DC/DC converters.

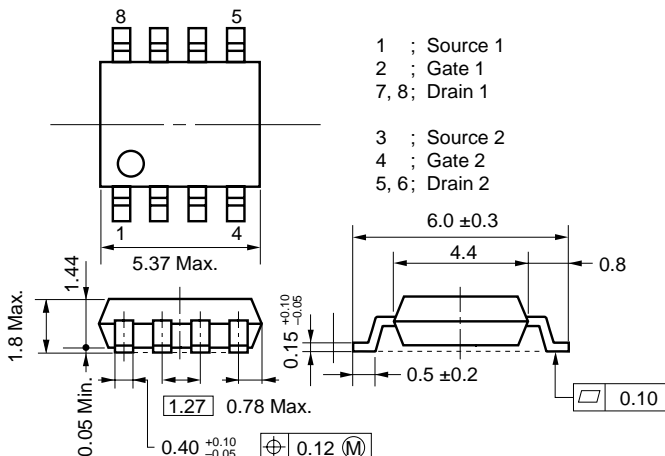
FEATURES

- Dual chip type
- Low on-resistance
 $R_{DS(on)1} = 110 \text{ m}\Omega \text{ TYP. (} V_{GS} = 10 \text{ V, } I_D = 2.5 \text{ A)}$
 $R_{DS(on)2} = 170 \text{ m}\Omega \text{ TYP. (} V_{GS} = 4 \text{ V, } I_D = 2.5 \text{ A)}$
- Low input capacitance $C_{iss} = 190 \text{ pF TYP.}$
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1759G	Power SOP8

PACKAGE DRAWING (Unit : mm)



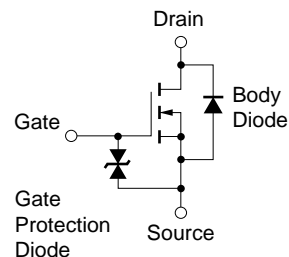
ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ }^\circ\text{C}$, All terminals are connected.)

Drain to Source Voltage ($V_{GS} = 0$)	V_{DSS}	60	V
Gate to Source Voltage ($V_{DS} = 0$)	V_{GSS}	±20	V
Drain Current (DC)	$I_{D(DC)}$	±5.0	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	±20	A
Total Power Dissipation (1 unit) ^{Note2}	P_T	1.7	W
Total Power Dissipation (2 unit) ^{Note2}	P_T	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note3}	I_{AS}	2.5	A
Single Avalanche Energy ^{Note3}	E_{AS}	0.625	mJ

- Notes
1. $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1 \%$
 2. Mounted on ceramic substrate of $1200 \text{ mm}^2 \times 1.7 \text{ mm}$
 3. Starting $T_{ch} = 25 \text{ }^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

EQUIVALENT CIRCUIT
(1/2 Circuit)

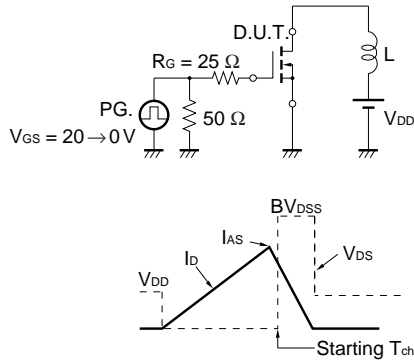


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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

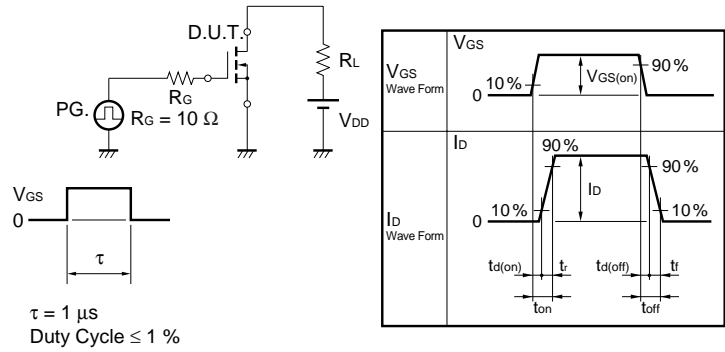
ELECTRICAL CHARACTERISTICS (T_A = 25 °C, All terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 2.5 A		110	150	mΩ
	R _{DS(on)2}	V _{GS} = 4 V, I _D = 2.5 A		170	240	mΩ
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.0	1.7	2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 2.5 A	2.0	3.9		S
Drain Leakage Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 10 V		190		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		100		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		36		pF
Turn-on Delay Time	t _{d(on)}	I _D = 2.5 A		6		ns
Rise Time	t _r	V _{GS(on)} = 10 V		50		ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = 15 V		80		ns
Fall Time	t _f	R _G = 10 Ω		50		ns
Total Gate Charge	Q _G	I _D = 5.0 A		8		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 24 V		1		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = 10 V		2.4		nC
Body Diode forward Voltage	V _{F(S-D)}	I _F = 5.0 A, V _{GS} = 0 V		0.9		V
Reverse Recovery Time	t _{rr}	I _F = 5.0 A, V _{GS} = 0 V		40		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		50		nC

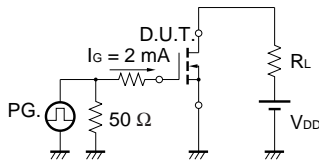
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



[MEMO]

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